

Silicon planar diode Rev. 02 — 31 August 2004

Product data sheet



1.1 General description

Planar high performance band-switching diode in a small rectangular SOT23 SMD plastic package.

1.2 Features

- Continuous reverse voltage: max. 35 V
- Continuous forward current: max. 100 mA
- Low diode capacitance: max. 1.0 pF
- Low diode forward resistance: max. 0.7Ω .

1.3 Applications

Band switching.

Pinning information 2.

Table 1: **Pinning**

Pin	Description	Simplified outline	Symbol		
1	anode		_		
2	not connected	3	3		
3	cathode	1 2	12 sym044		

Ordering information 3.

Table 2: Ordering information

Type number	Package		
	Name	Description	Version
BAT18	-	plastic surface mounted package; 3 leads	SOT23





4. Marking

Table 3: Marking

Type number	Marking code [1]
BAT18	10*

- [1] * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China.

5. Limiting values

Table 4: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	continuous reverse voltage		-	35	V
I _F	continuous forward current		-	100	mA
T _{stg}	storage temperature		–55	+125	°C
Tj	junction temperature		-	125	°C

6. Thermal characteristics

Table 5: Thermal characteristics

 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-tp)}$	thermal resistance from junction to tie-point		330	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		[<u>1</u>] 500	K/W

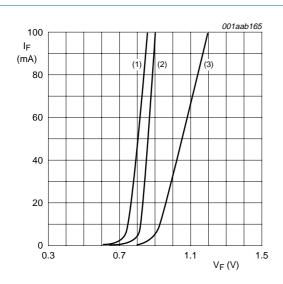
^[1] Device mounted on a FR4 printed-circuit board.

7. Characteristics

Table 6: Electrical characteristics

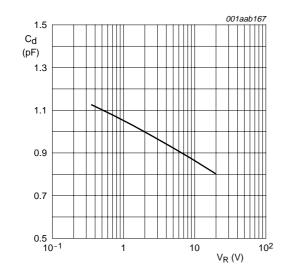
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage	I _F = 100 mA; see <u>Figure 1</u>	-	-	1.2	V
I _R	reverse current	see Figure 2				
		V _R = 20 V	-	-	100	nA
		V _R = 20 V; T _j = 60 °C	-	-	1	μΑ
C _d	diode capacitance	V _R = 20 V; f = 1 MHz; see <u>Figure 3</u>	-	8.0	1.0	pF
r _D	diode forward resistance	I _F = 5 mA; f = 200 MHz; see <u>Figure 4</u>	-	0.5	0.7	Ω

Silicon planar diode



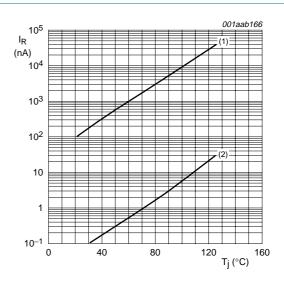
- (1) $T_i = 60 \,^{\circ}\text{C}$; typical values.
- (2) T_i = 25 °C; typical values.
- (3) $T_i = 25 \,^{\circ}C$; maximum values.

Fig 1. Forward current as a function of forward voltage.



f = 1 MHz; $T_i = 25 \,^{\circ}\text{C}$.

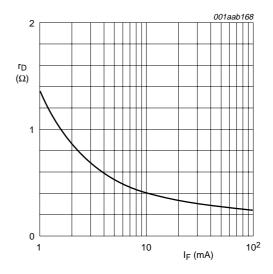
Fig 3. Diode capacitance as a function of reverse voltage; typical values.



 $V_R = 20 \text{ V}.$

- (1) maximum values.
- (2) typical values.

Fig 2. Reverse current as a function of junction temperature.



f = 200 MHz; $T_i = 25 \,^{\circ}\text{C}$.

Fig 4. Diode forward resistance as a function of forward current; typical values.

Package outline

Plastic surface mounted package; 3 leads

SOT23

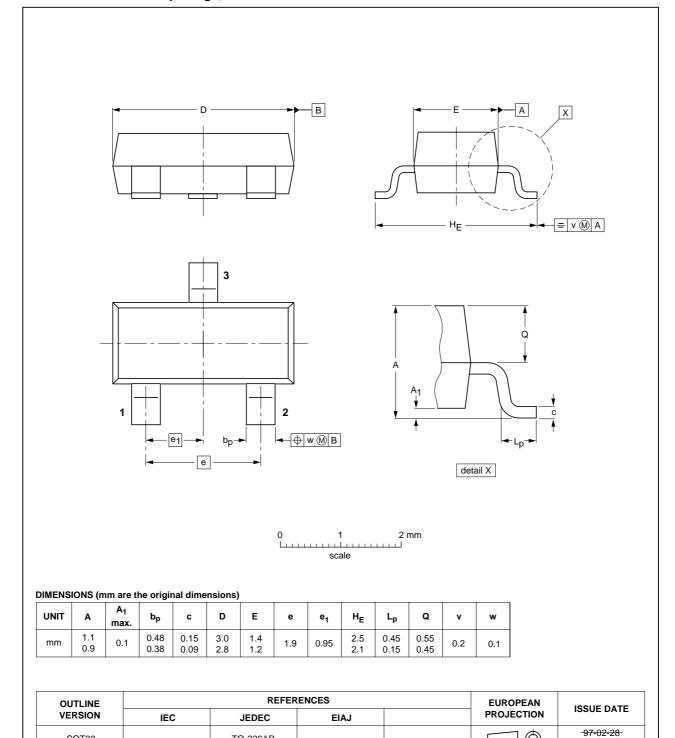


Fig 5. Package outline.

SOT23

99-09-13

TO-236AB

Silicon planar diode



9. Revision history

Table 7: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
BAT18_2	20040831	Product data sheet	-	9397 750 13385	BAT18_1
Modifications: • The format of this data sheet has been redesigned to comply with the new presentation information standard of Philips Semiconductors.		v presentation and			
	• <u>Table 3</u> : m	arking code changed.			
BAT18_1	19960313	Product specification	-	not applicable	-

Philips Semiconductors

BAT18

Silicon planar diode

10. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

- [1] Please consult the most recently issued data sheet before initiating or completing a design.
- [2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- [3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

11. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

12. Disclaimers

Life support — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

13. Contact information

For additional information, please visit: http://www.semiconductors.philips.com
For sales office addresses, send an email to: sales.addresses@www.semiconductors.philips.com



Silicon planar diode

14. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications
2	Pinning information 1
3	Ordering information
4	Marking 2
5	Limiting values 2
6	Thermal characteristics 2
7	Characteristics 2
8	Package outline 4
9	Revision history 5
10	Data sheet status 6
11	Definitions 6
12	Disclaimers 6
13	Contact information 6



All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Date of release: 31 August 2004 Document number: 9397 750 13385

